

BUK7635-100A

N-channel TrenchMOS standard level FET

Rev. 02 — 18 February 2011

Product data sheet

1. Product profile

1.1 General description

Standard level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

1.2 Features and benefits

- AEC Q101 compliant
- Low conduction losses due to low on-state resistance
- Suitable for standard level gate drive sources
- Suitable for thermally demanding environments due to 175 °C rating

1.3 Applications

- 12 V, 24 V and 42 V loads
- Automotive and general purpose power switching
- Motors, lamps and solenoids

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DS}	drain-source voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}$	-	-	100	V
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C; see <u>Figure 1</u> ; see <u>Figure 3</u>	-	-	41	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	-	149	W
Static char	acteristics					
R _{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A};$ $T_j = 175 ^{\circ}\text{C}; \text{ see } \frac{\text{Figure 12}}{\text{Figure 13}};$	-	-	88	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A};$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 12}}{\text{see } \frac{\text{Figure 13}}{\text{Figure 13}};$	-	21	35	mΩ
Avalanche	ruggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$\begin{split} I_D &= 25 \text{ A; } V_{sup} \leq 100 \text{ V;} \\ R_{GS} &= 50 \text{ \Omega; } V_{GS} = 10 \text{ V;} \\ T_{j(init)} &= 25 \text{ °C; unclamped} \end{split}$	-	-	110	mJ



2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		
2	D	drain	mb	D
3	S	source		
mb	D	mounting base; connected to drain		mbb076 S
			SOT404 (D2PAK)	

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BUK7635-100A	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
-	raiailietei		IVIIII		
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	100	V
V_{DGR}	drain-gate voltage	$R_{GS} = 20 \text{ k}\Omega$	-	100	V
V _{GS}	gate-source voltage		-20	20	V
I _D	drain current	T_{mb} = 25 °C; V_{GS} = 10 V; see <u>Figure 1</u> ; see <u>Figure 3</u>	-	41	Α
		T_{mb} = 100 °C; V_{GS} = 10 V; see Figure 1	-	29	Α
I _{DM}	peak drain current	T_{mb} = 25 °C; pulsed; $t_p \le 10 \mu s$; see Figure 3	-	165	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	149	W
T _{stg}	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
Source-drain	diode				
Is	source current	T _{mb} = 25 °C	-	41	Α
I _{SM}	peak source current	pulsed; $t_p \le 10 \mu s$; $T_{mb} = 25 \text{ °C}$	-	165	Α
Avalanche ru	ggedness				
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	I_D = 25 A; V_{sup} ≤ 100 V; R_{GS} = 50 Ω; V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; unclamped	-	110	mJ

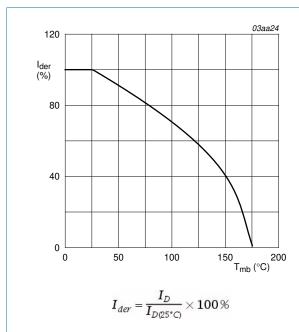
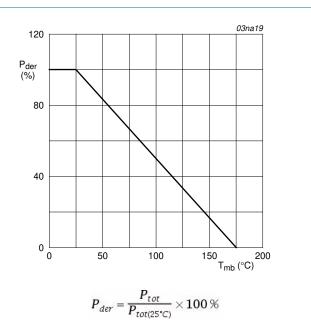
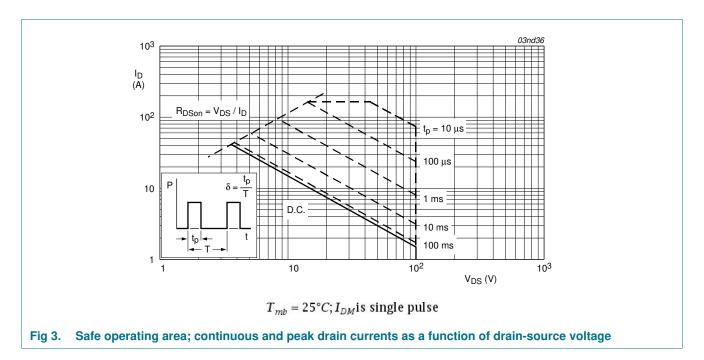


Fig 1. Normalized continuous drain current as a function of mounting base temperature



2. Normalized total power dissipation as a function of mounting base temperature

N-channel TrenchMOS standard level FET



5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	-	1	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	mounted on a printed-circuit board; minimum footprint	-	50	-	K/W

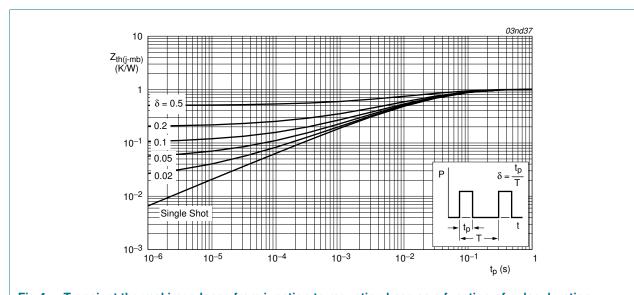


Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

6. Characteristics

Table 6. Characteristics

Symbol	Parameter Parameter	Conditions	Min	Тур	Max	Unit
•	racteristics	Conditions	IVIIII	iyp	IVIAA	Oilit
	drain-source	L 0.25 A: V 0.V: T 25 °C	100	_		V
(B11)B00	breakdown voltage	$I_D = 0.25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$ $I_D = 0.25 \text{ A}; V_{GS} = 0 \text{ V}; T_i = -55 \text{ °C}$	89		<u>-</u>	V
V		<u> </u>	2			V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}$; $V_{DS} = V_{GS}$; $T_j = 25 \text{ °C}$; see <u>Figure 11</u>	2	3	4	V
		$I_D = 1 \text{ mA}$; $V_{DS} = V_{GS}$; $T_j = -55 \text{ °C}$; see <u>Figure 11</u>	-	-	4.4	V
		$I_D = 1$ mA; $V_{DS} = V_{GS}$; $T_j = 175$ °C; see Figure 11	1	-	-	V
I _{DSS}	drain leakage current	$V_{DS} = 100 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.05	10	μΑ
		V _{DS} = 100 V; V _{GS} = 0 V; T _j = 175 °C	-	-	500	μΑ
I _{GSS}	gate leakage current	$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	2	100	nA
		V _{GS} = -20 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
R _{DSon} drain-source on-state resistance		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 175 ^{\circ}\text{C};$ see Figure 12; see Figure 13	-	-	88	mΩ
	V_{GS} = 10 V; I_D = 25 A; T_j = 25 °C; see Figure 12; see Figure 13	-	21	35	mΩ	
Dynamic	characteristics					
C _{iss}	input capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 25 \text{ V}; f = 1 \text{ MHz};$	-	1900	2535	pF
C _{oss}	output capacitance	T _j = 25 °C; see <u>Figure 14</u>	-	250	301	рF
C _{rss}	reverse transfer capacitance		-	150	205	pF
$t_{d(on)}$	turn-on delay time	$V_{DS} = 30 \text{ V}; R_L = 1.2 \Omega; V_{GS} = 10 \text{ V}; R_{G(ext)} = 10 \Omega; T_j = 25 ^{\circ}C$	-	15	-	ns
t _r	rise time	$V_{DS} = 30 \text{ V}; V_{GS} = 10 \text{ V}; R_{G(ext)} = 10 \Omega;$ $T_i = 25 \text{ °C}$	-	67	-	ns
t _{d(off)}	turn-off delay time	$V_{DS} = 30 \text{ V}; V_{GS} = 10 \text{ V}; R_{G(ext)} = 10 \Omega$	-	56	-	ns
t _f	fall time		-	35	-	ns
L _D	internal drain inductance	from drain lead 6 mm from package to centre of die; $T_i = 25$ °C	-	4.5	-	nΗ
		from upper edge of drain mounting base to centre of die; T _j = 25 °C	-	2.5	-	nΗ
L _S	internal source inductance	from source lead to source bond pad; $T_j = 25 ^{\circ}\text{C}$	-	7.5	-	nΗ
Source-di	rain diode					
V_{SD}	source-drain voltage	$I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C};$ see <u>Figure 15</u>	-	0.85	1.2	V
t _{rr}	reverse recovery time	$I_S = 20 \text{ A}; dI_S/dt = -100 \text{ A}/\mu\text{s};$	-	67	-	ns
Q _r	recovered charge	$V_{GS} = -10 \text{ V}; V_{DS} = 30 \text{ V}; T_j = 25 \text{ °C}$	-	220	-	nC

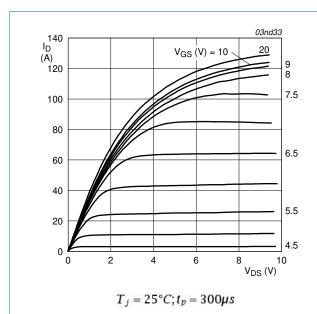


Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values

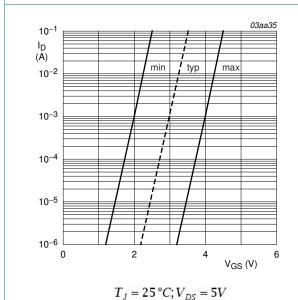
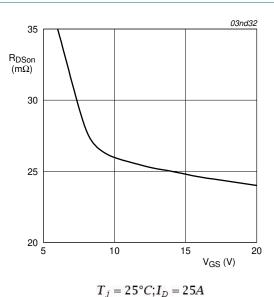
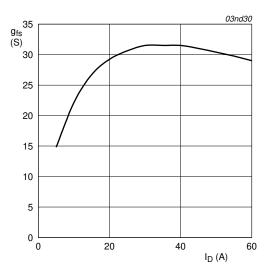


Fig 7. Sub-threshold drain current as a function of gate-source voltage



 $I_j = 25 \text{ C}, I_D = 25A$

Fig 6. Drain-source on-state resistance as a function of gate-source voltage; typical values



 $T_j = 25^{\circ}C; V_{DS} = 25V$

Fig 8. Forward transconductance as a function of drain current; typical values

N-channel TrenchMOS standard level FET

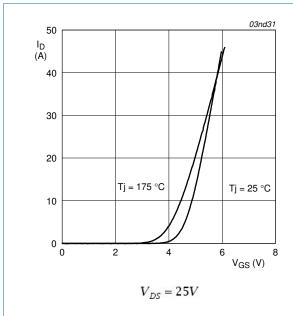


Fig 9. Transfer characteristics: drain current as a function of gate-source voltage; typical values

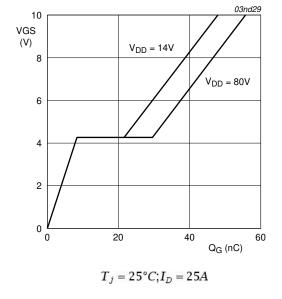


Fig 10. Gate-source voltage as a function of turn-on gate charge; typical values

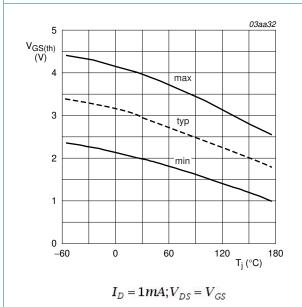


Fig 11. Gate-source threshold voltage as a function of junction temperature

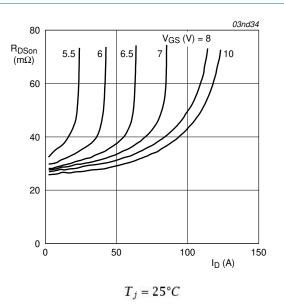


Fig 12. Drain-source on-state resistance as a function of drain current; typical values

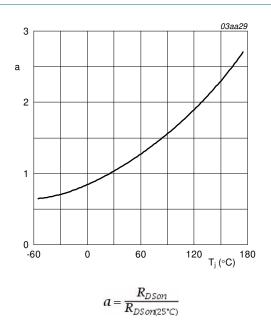


Fig 13. Normalized drain-source on-state resistance factor as a function of junction temperature

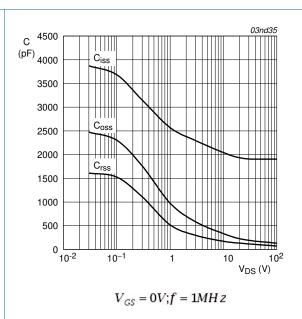


Fig 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

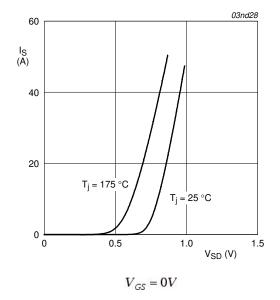


Fig 15. Reverse diode current as a function of reverse diode voltage; typical values

7. Package outline

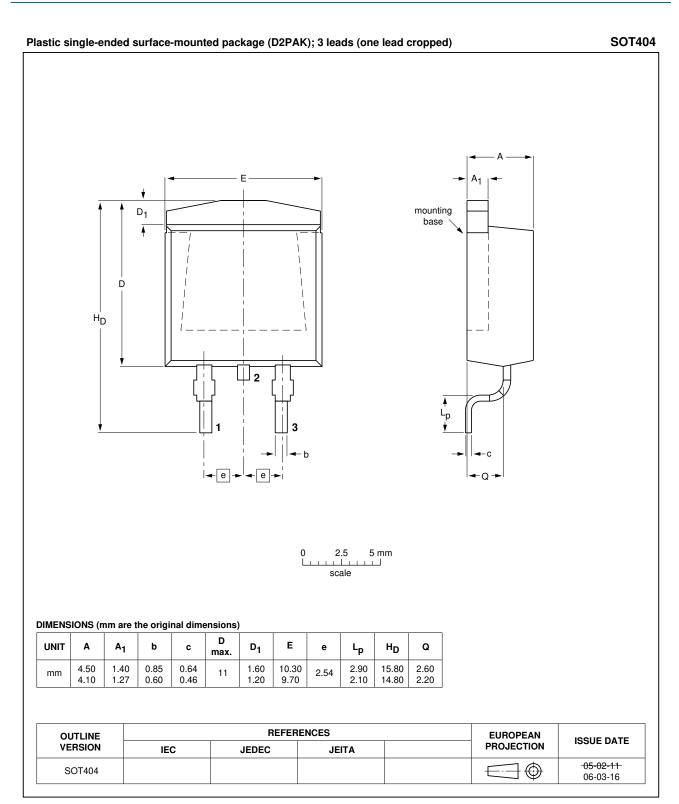


Fig 16. Package outline SOT404 (D2PAK)

N-channel TrenchMOS standard level FET

8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BUK7635-100A v.2	20110218	Product data sheet	-	BUK7535_7635_100A v.1
Modifications:		nis data sheet has been ro XP Semiconductors.	edesigned to comply	with the new identity
	 Legal texts have 	e been adapted to the ne	w company name wh	ere appropriate.
	 Type number B 	UK7635-100A separated	from data sheet BUK	(7535_7635_100A v.1.
BUK7535_7635_100A v.1	20010202	Product specification	-	-

9. Legal information

9.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design
- [2] The term 'short data sheet' is explained in section "Definitions"
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BUK7635-100A

N-channel TrenchMOS standard level FET

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N-channel TrenchMOS standard level FET

11. Contents

1	Product profile
1.1	General description1
1.2	Features and benefits1
1.3	Applications1
1.4	Quick reference data1
2	Pinning information2
3	Ordering information2
4	Limiting values3
5	Thermal characteristics4
6	Characteristics5
7	Package outline9
8	Revision history10
9	Legal information11
9.1	Data sheet status
9.2	Definitions11
9.3	Disclaimers
9.4	Trademarks12
10	Contact information12